

Back to Basic

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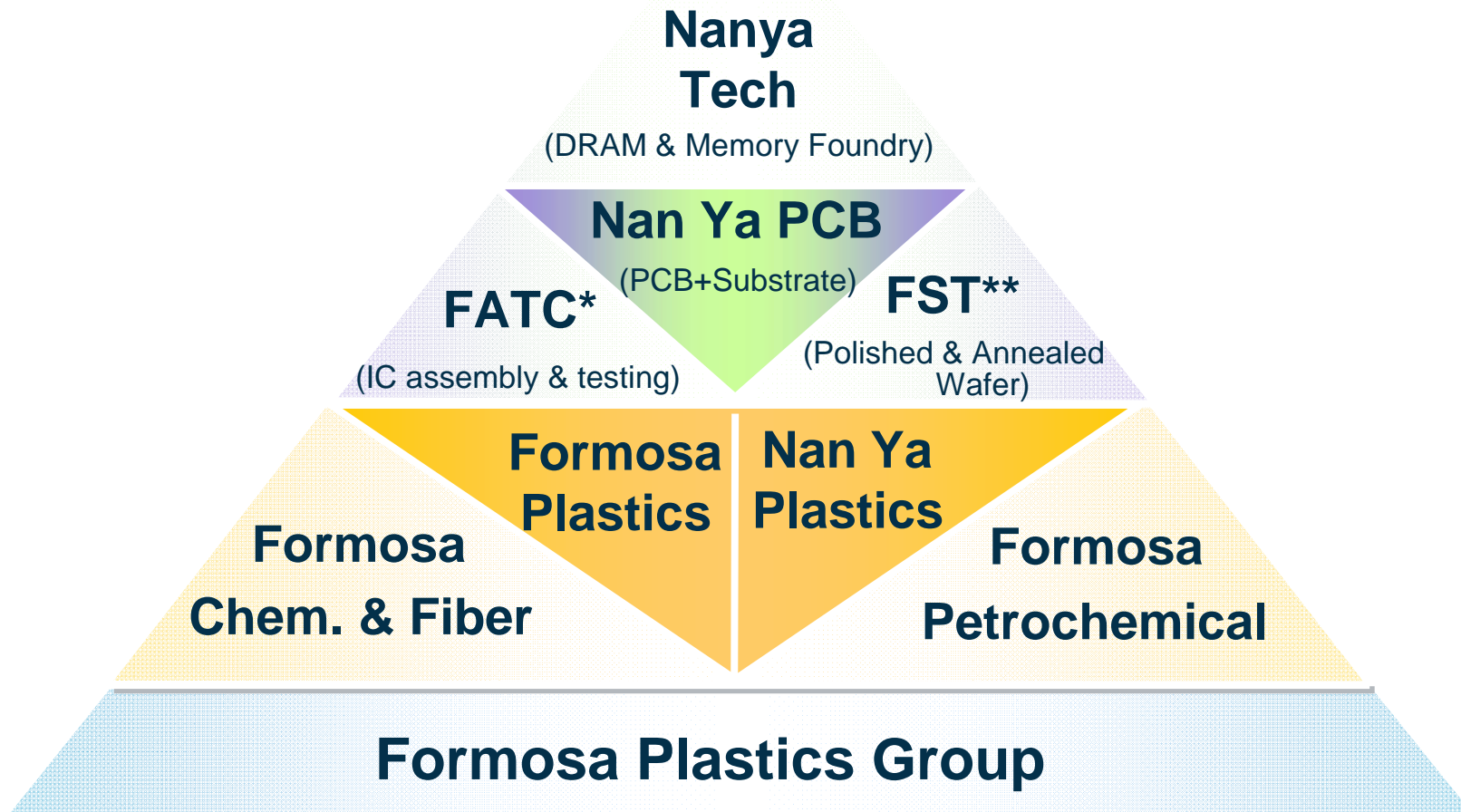
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NANYA
Technology Corporation

Company Overview

Nanya Technology Corporation
June 2008

A Member of the Formosa Group

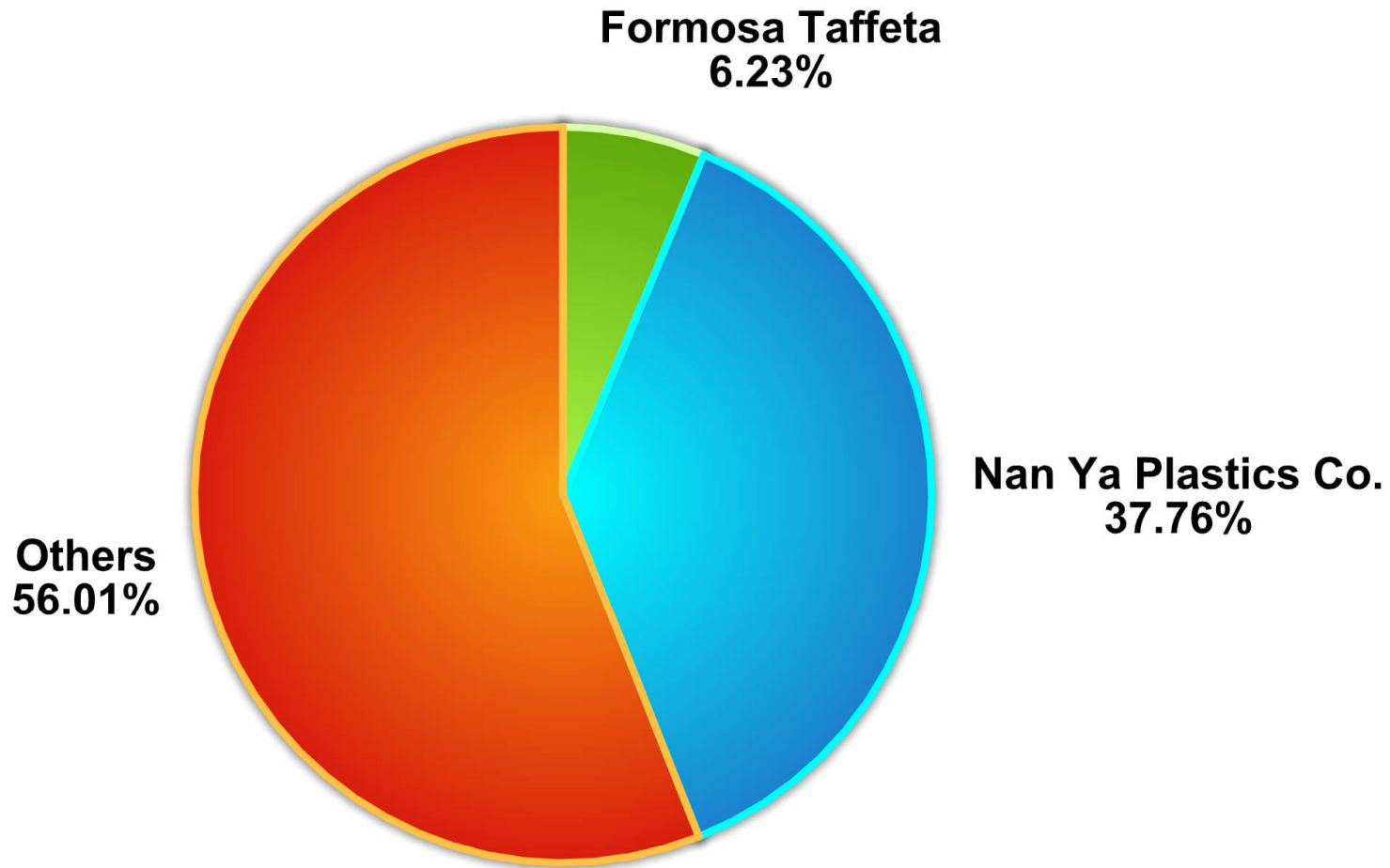


* FATC = Formosa Advanced Technology Co.

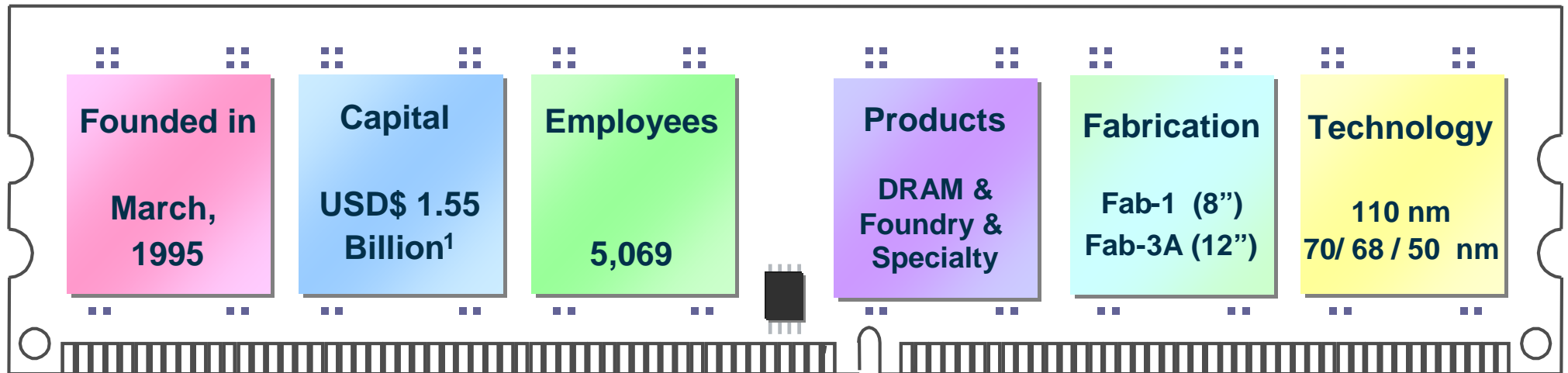
** FST = Formosa Sumco Technology



Shareholders



Nanya at a Glance



Note:

1. US\$1=NT\$ 30.35 as of June 5, 2008



Company Milestones

- 1995** • Nanya Technology Corporation founded
- 1996** • Signed .36/.32 μ m technology license agreements with OKI
- 1998** • Signed .2/.175 μ m technology license agreements with IBM
- 1999** • 0.20 μ m 64Mb SDRAM mass production started
- 2000** • IPO
- 2002** • Set up Nanya Technology Japan and Signed JD and JV agreement with Infineon
- 2004** • Qualification of DDR2 products
- 2005** • Successful qualification of 90nm technology
 - Signed 60nm technology co-development agreement with Infineon
- 2006** • Nanya FAB-3A (300mm) groundbreaking ceremony
 - Successful qualification of 70/75nm technology with Qimonda
- 2007** • FAB-3A clean room construction and FAB-3A equipment move-in
 - Pilot run successful in FAB-3A, 70nm wafer starts in 3Q
- 2008** • Signed JV agreement to create MeiYa Technology Corp. with Micron

Nanya Named World's 93rd IT Company

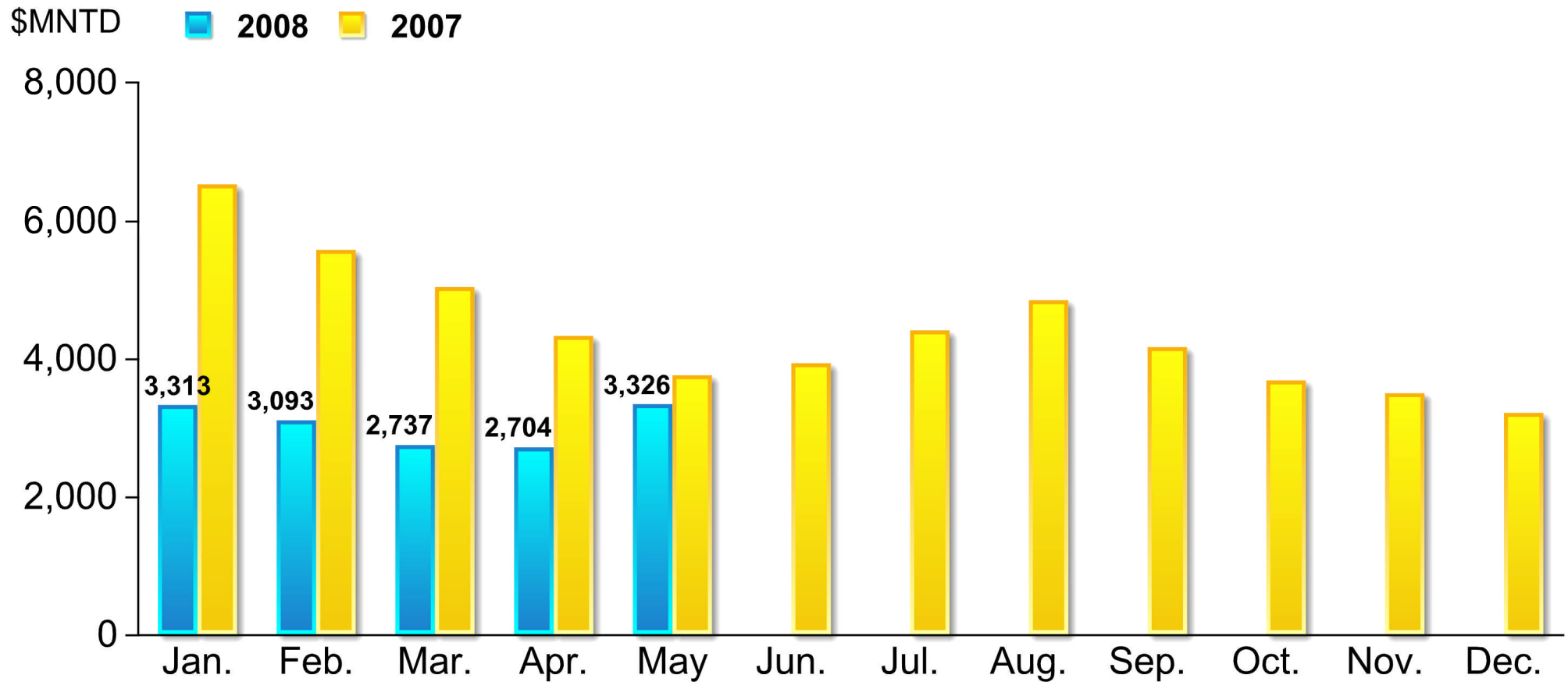
BusinessWeek

TheFutureofTech | The InfoTech 100

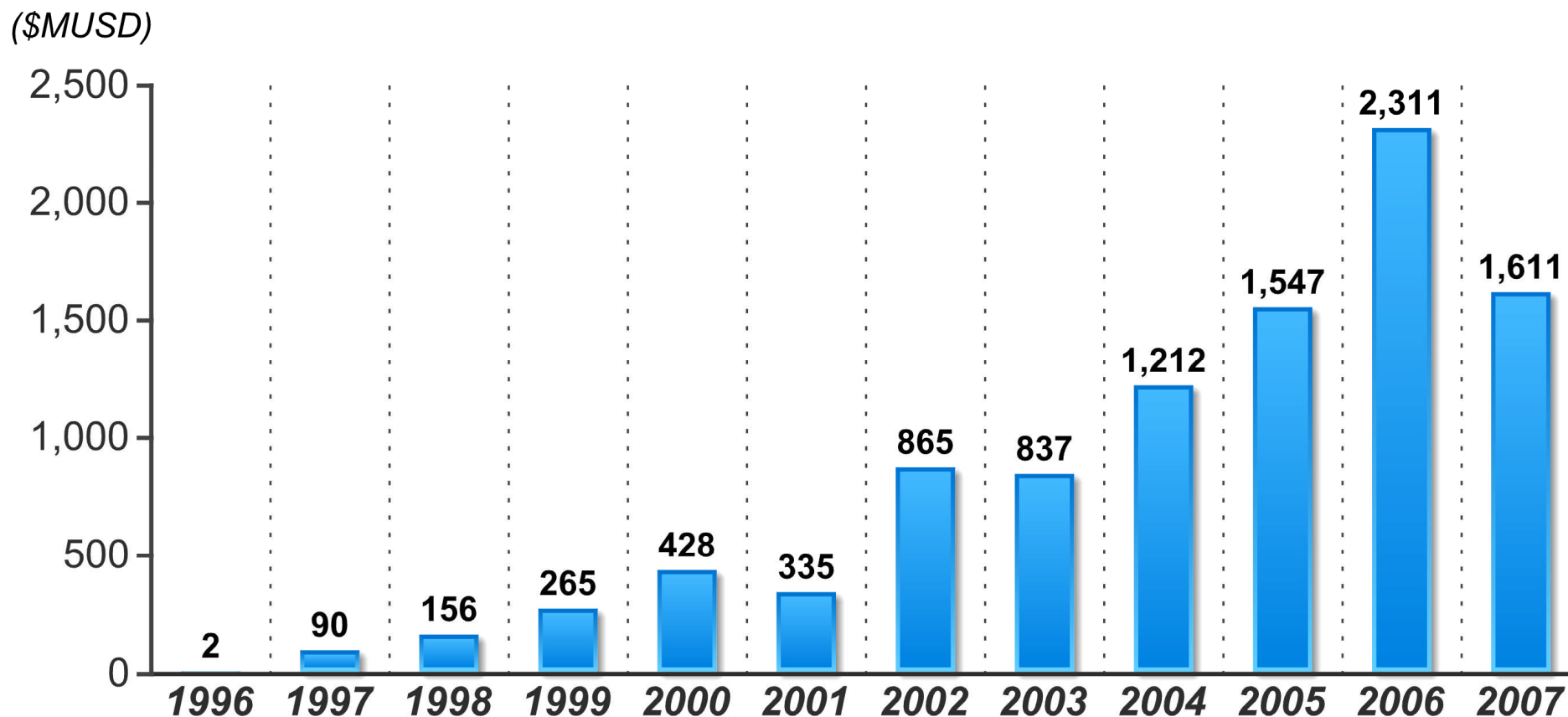
Rank ▲	Company Name	Industry*	Country	Revenues		Rev. Growth		Return on Equity		Shareholder Return		Profits Millions
				Millions	Rank	Percent	Rank	Percent	Rank	Percent	Rank	
85	TOKYO ELECTRON	SEMI	Japan	7,578.5	46	26	52	20	65	-18	98	812
86	DELTA ELECTRONICS	COMM	Taiwan	3,257.3	69	30	45	23	51	-4	85	351
87	AUTOMATIC DATA PROCESSING	SVCS	U.S.	8,569.1	42	14	84	21	62	1	76	1130
88	ADVANCED SEMICONDUCTOR ENG.	SEMI	Taiwan	3,108.9	72	20	62	26	35	-2	80	539
89	ROGERS COMMUNICATIONS	TELE	Canada	9,915.1	36	15	82	14	88	7	62	624
90	UNITED INTERNET	NET	Germany	2,136.7	84	17	75	41	14	3	71	219
91	SATYAM COMPUTER SERVICES	SVCS	India	2,118.7	85	31	43	23	46	3	72	422
92	NAN YA PCB	COMM	Taiwan	1,156.8	95	48	19	25	37	-8	90	317
93	NANYA TECHNOLOGY	SEMI	Taiwan	2,312.8	82	49	17	23	52	-17	97	539
94	ADOBE SYSTEMS	SOFT	U.S.	3,398.9	66	32	42	21	59	-10	91	799
95	HCL TECHNOLOGIES	SVCS	India	1,517.4	89	33	41	32	26	-11	92	330

* Resource: <http://www.businessweek.com/>

2008 Revenue Update



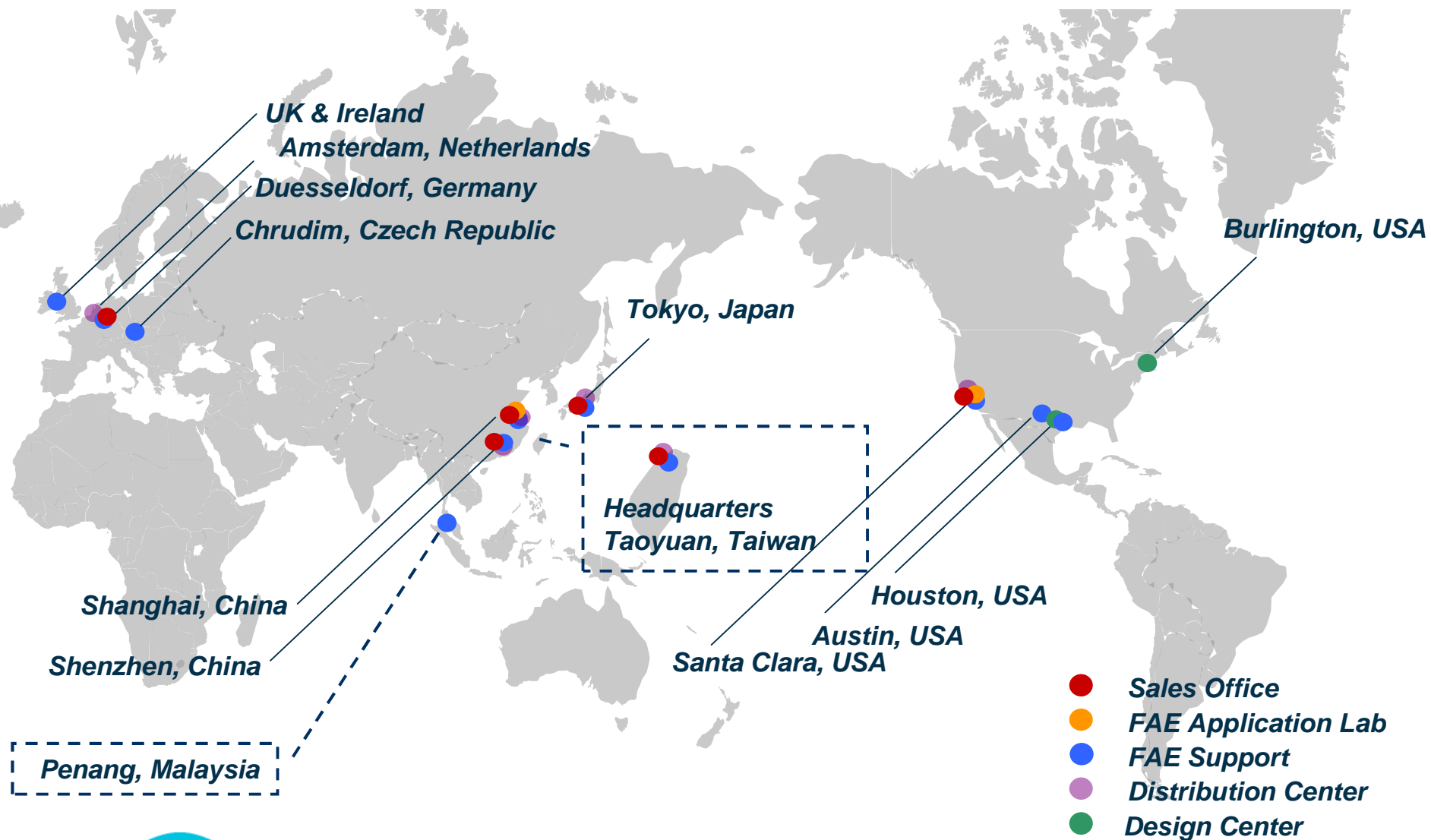
Annual Revenue Update



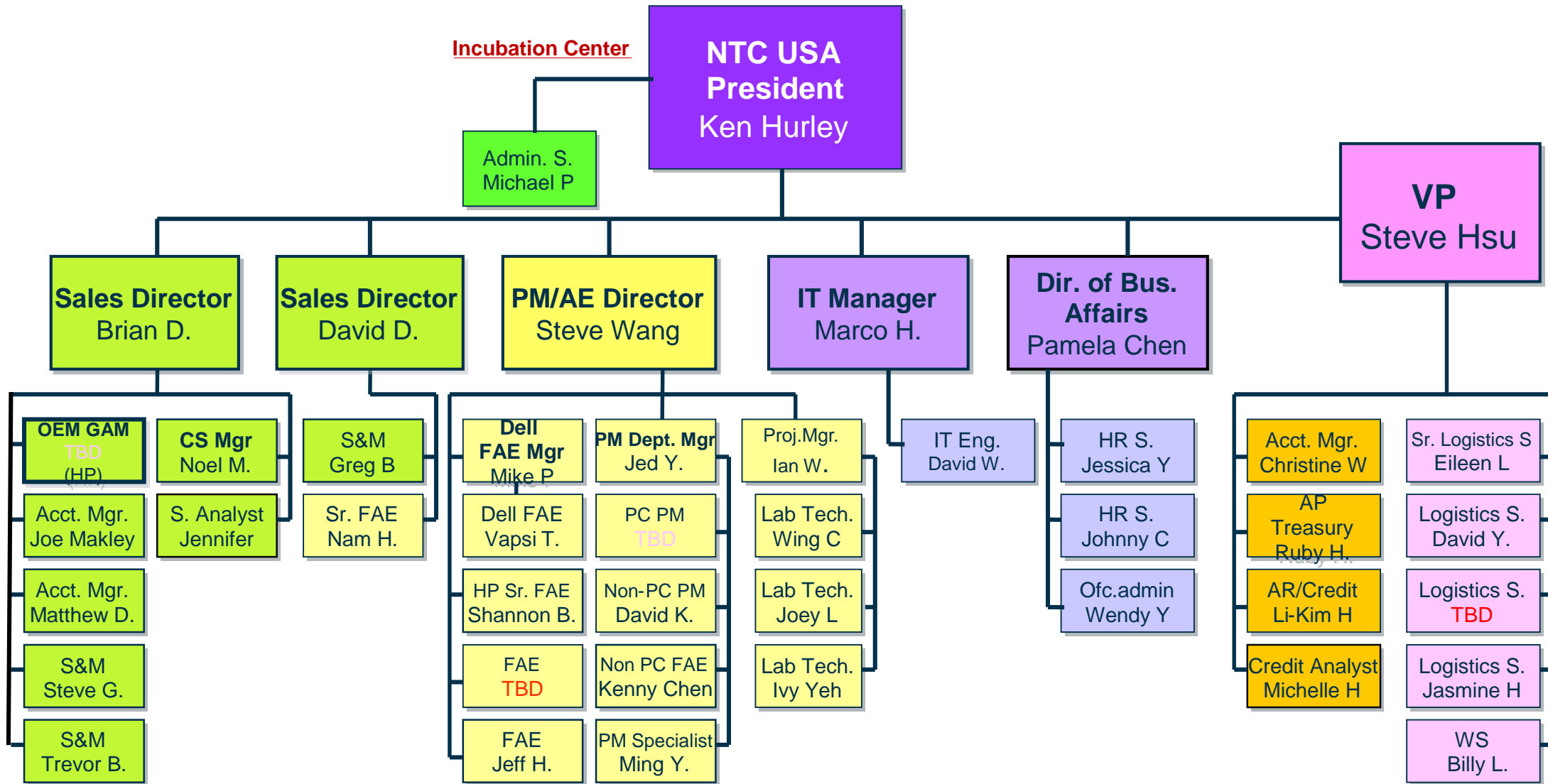
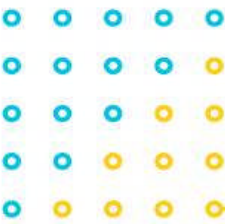
Note: US\$1 = NT\$32.842 as of Y2007 average

Global Reach

Global Service Network



Nanya Technology Corporation USA



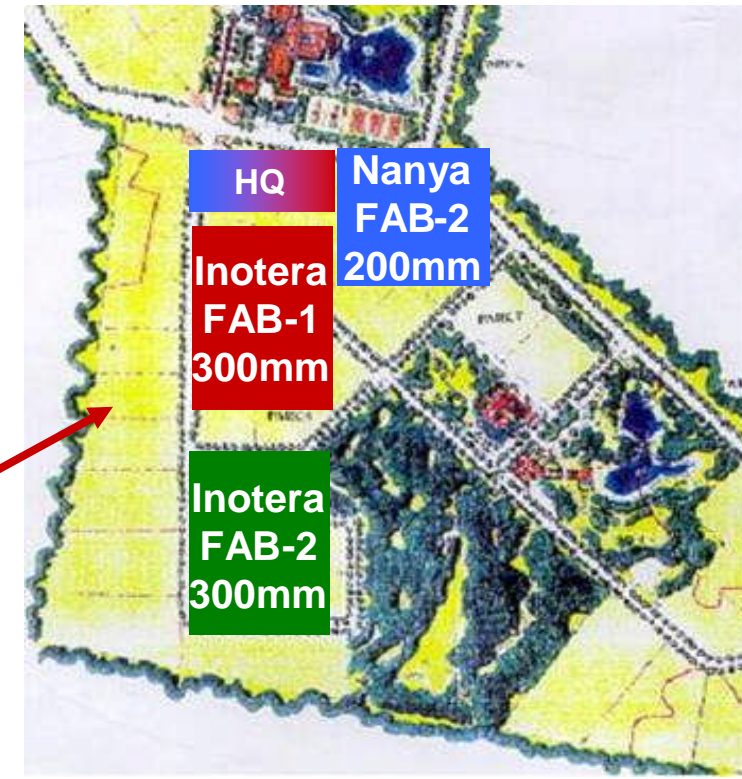
Headquarters in Taiwan



**Hwa-Ya Technology Park:
Total area 158 hectare**



**Nanya Tech & Inotera in Hwa-Ya:
Total area 8.7 hectare**



- In Operation
- In Operation
- Equipment Move-in

Nanya Fabs



Fab-1

Location : Taoyuan, Taiwan ,1996
Capacity : 32,000 wafers per month
Technology : 110nm
Product : DRAM, Foundry,
and Specialty products

Fab-3A

Location : Taishan, Taiwan
Capacity : 62,000 wafers per month
Technology : 70nm/68nm/50nm
Product : DRAM



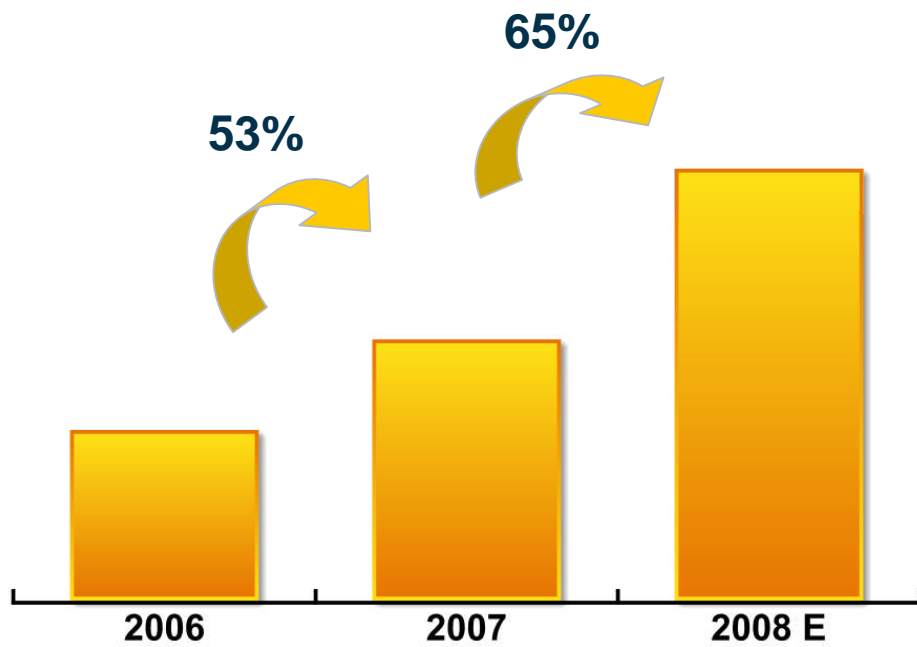
Nanya Fab-3A (300mm)

Location	: Taishan, Taiwan
Total Area	: 4.9 hectare
Investment	: Total NTD 83.9 billion
Schedule	: Mar'06 Groundbreaking Mar'07 Clean Room Construction May'07 Equipment Move-in Pilot Run (90nm), full line test completed with excellent yields 4Q '07 Mass Production Wafer Start (70nm) Complete 70nm 1Gb first phase in 2Q'08
Targeted Capacity	: 30,000 WSPM (Phase 1)
Max. Capacity	: 62,000 WSPM
Technology	: 70nm / 58nm
Product	: DRAM

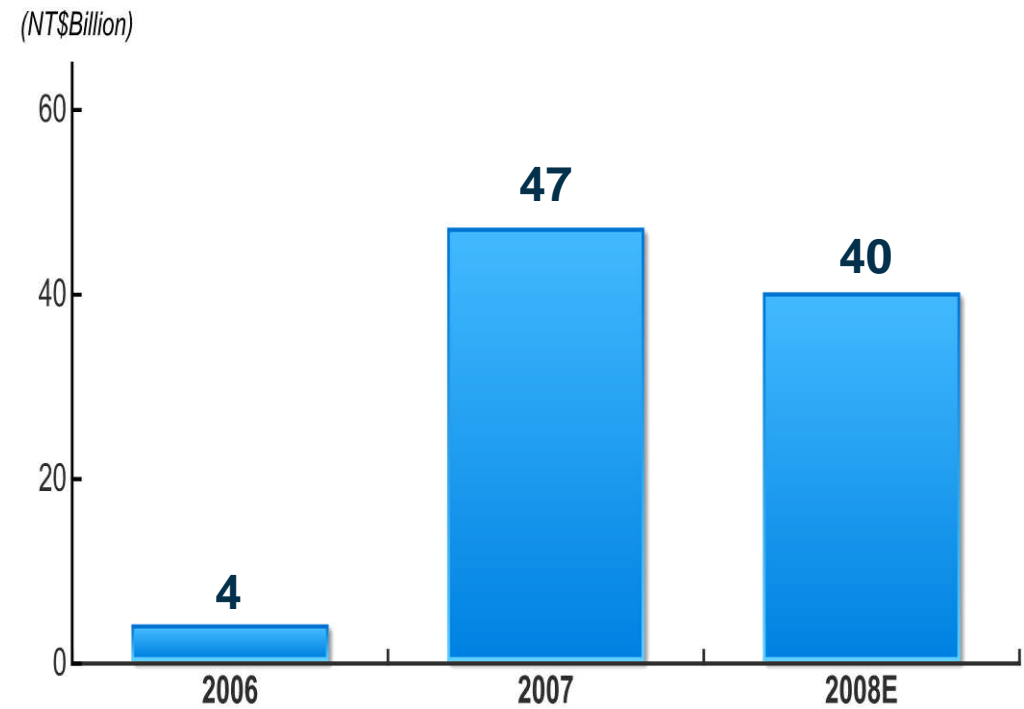


2008 Business Outlook

Annual Bit Growth



Capex





Nanya & Qimonda Cooperation

Nanya & Qimonda* Cooperation

NTC-QAG* JV (Inotera Memories, Inc.):

- ❑ 120K wafer starts per month from Fab-1 + Fab-2 combined achieved in Sep. 2007
(original schedule: Dec '07)
- ❑ 1Gb DDR3 DRAM product is expected to start pilot run in 70nm technology in 1Q, 2008.
- ❑ Fully convert wafer starts to 1Gb DDR2 DRAM products in 70nm shrink technology in Q3, 2008.
- ❑ 58nm process trench technology is scheduled to pilot run in 2H of CY2008

NTC-QAG* JD:

- ❑ JD 90/70/58nm technology
- ❑ Share IP ownership



* The former Memory Products Group of Infineon Technologies



Inotera Milestones

- **2002**

- Nanya and Infineon signed JD & JV Agreement
- Groundbreaking ceremony of Fab-1

- **2003**

- Completion of Fab-1 construction & equipment move-in

- **2004**

- First wafer (256Mb DDR1) manufactured
- Grand opening of HQ & Fab-1
- Reached 24K WSPM of Fab-1

- **2005**

- Groundbreaking of Fab-2
- Reached 60K WSPM of Fab-1

- **2006**

- IPO
- GDR offering
- 90nm conversion completed
- Fab-2 equipment & tool move-in

- **2007**

- Fab-2 Grand opening
- First silicon start in 70nm technology
- Completed Fab-2 equipment move-in and achieved 120K WSPM per month of combined capacity at Fab-1 and Fab-2
- Shipment qualification of new 70/75 technology in both 512 Mb and 1Gb DDR2 products and mass production



Nanya & Micron Partnership

Nanya & Micron* Partnership

NTC – Micron JV (MeiYa Technology Corp.):

❑ Joint Venture Agreement :

Signed on April 21, 2008

❑ New Venture Company:

MeiYa Technology Corporation

❑ Production Site:

Upgrade Nanya's current 200 mm fab to 300 mm fab

❑ Capital:

Each parent company injects US\$550 million in cash by the end of 2009

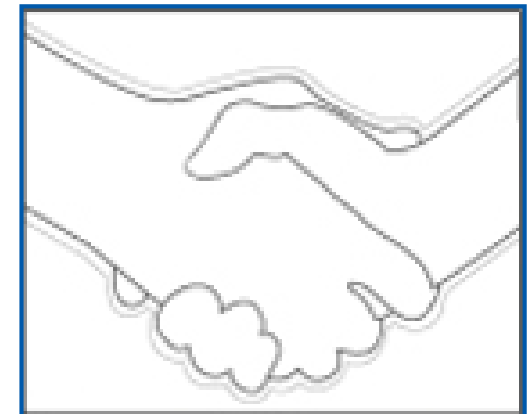
❑ Shareholder Structure:

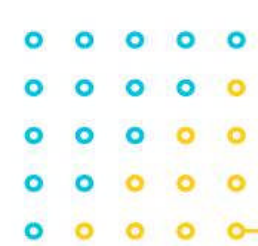
Each parent company holds 50% initially

❑ Production Schedule:

68nm process stack technology is scheduled to pilot run in 1H 2009

Monthly capacity is expected to 45K





Product Roadmap

Q2 2008

Capacity and Technology Mix

Quarterly wafer input 12-inch equiv.(K pcs)

